

Product Overview

NTM50D7N04C: Power MOSFET, Single N-Channel, 40 V, 0.67 mOhms, 420 A

For complete documentation, see the data sheet.

This N-Channel MV MOSFET is produced using ON Semiconductor's advanced Power Trench process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

Features

- Small Footprint (8x8 mm)
- Low $R_{DS(on)}$
- Low QG and Capacitance
- RoHS Compliant

Applications

- Battery Switch
- Switching power supplies
- Load Switch

Benefits

- Compact Design
- Minimize Conduction Losses
- Minimize Driver Losses

End Products

- AC-DC Power Supplies
- Motor Control

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(sat)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5V$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5V$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10V$ (mΩ)	Q_g Typ @ $V_{GS} = 4.5V$ (nC)	Q_g Typ @ $V_{GS} = 10V$ (nC)	C_{iss} Typ (pF)	Package Type
NTM50D7N04CTXG	1.8484	Pb-free Halide free	Active	N-Channel	Single	40	20	4	420	4.9			0.67		140	9230	DFN W-8

For more information please contact your local sales support at www.onsemi.com.

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